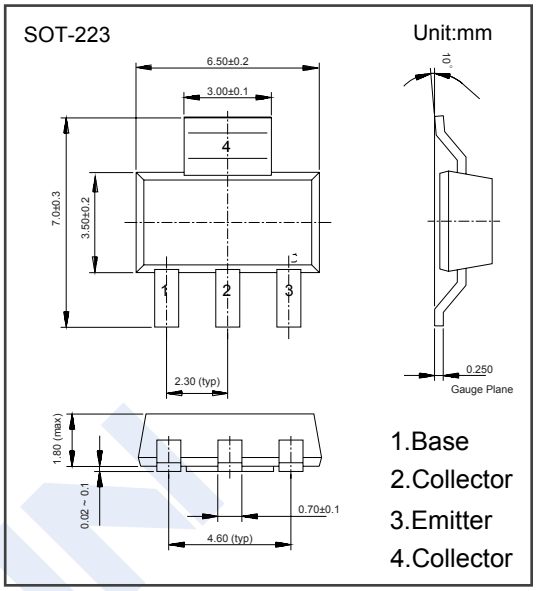
PNP Transistors

CZT5401 (KZT5401)



■ Features

- High Voltage
- High Voltage Amplifier Application

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-160	V
Collector - Emitter Voltage	V_{CEO}	-150	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-0.6	A
Collector Power Dissipation	P_C	1	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	125	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100uA， I_E= 0	-160			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA， I_B= 0	-150			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 uA， I_C= 0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -120 V , I_E= 0			-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -4V , I_C=0			-50	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B=-1mA			-0.2	V
		I_C=-50 mA, I_B=-5mA			-0.5	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-10 mA, I_B=-1mA			-1	
		I_C=-50 mA, I_B=-5mA			-1	
DC current gain	$h_{FE(1)}$	V_{CE}= -5V, I_C= -1mA	50			
	$h_{FE(2)}$	V_{CE}= -5V, I_C= -10mA	60		300	
	$h_{FE(3)}$	V_{CE}= -5V, I_C= -50mA	50			
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz			6	pF
Transition frequency	f_T	V_{CE}= -10V, I_C= -10mA,f=100MHz	100		300	MHz